

FIG. 1A

FORMATION OF AMORPHOUS SILICON FILM AND
INTRODUCTION OF N1 ELEMENT

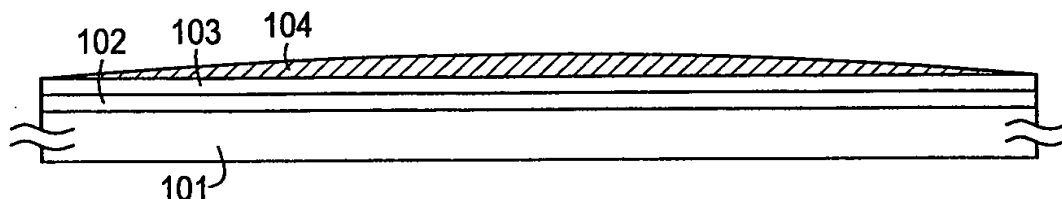


FIG. 1B

HEAT TREATMENT FOR CRYSTALLIZATION

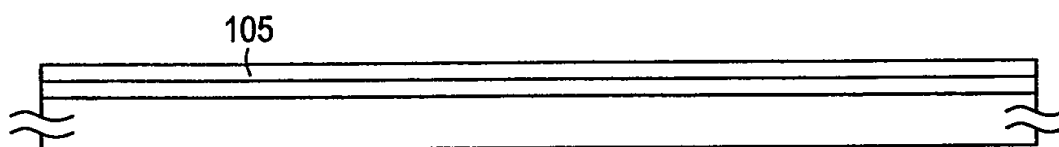


FIG. 1C

IRRADIATION OF LASER LIGHT

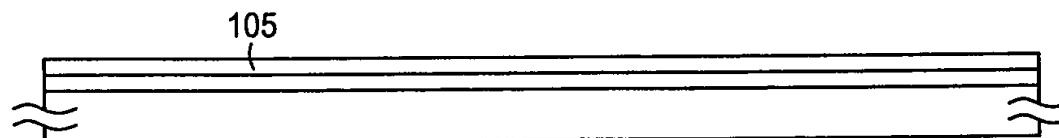


FIG. 1D

FORMATION OF WET OXIDE FILM CONTAINING FLUORITE

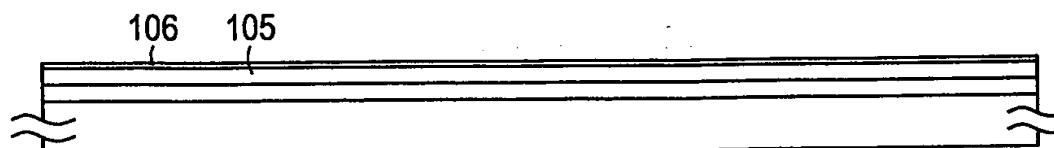
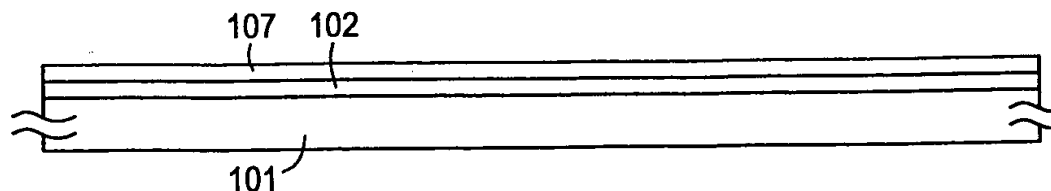


FIG. 1E

REMOVAL OF OXIDE FILM CONTAINING NI



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FIG. 2A

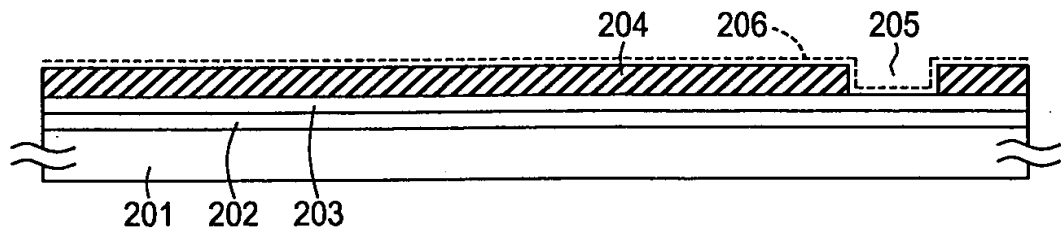


FIG. 2B

HEAT TREATMENT FOR CRYSTALLIZATION

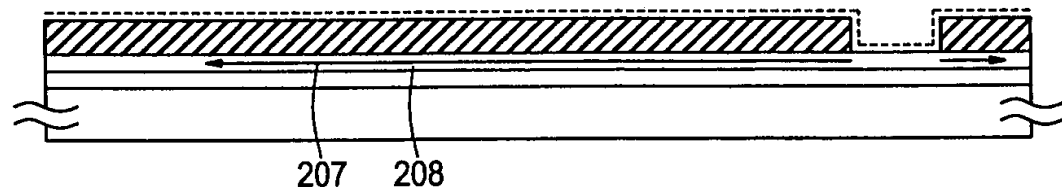


FIG. 2C

IRRADIATION OF LASER LIGHT

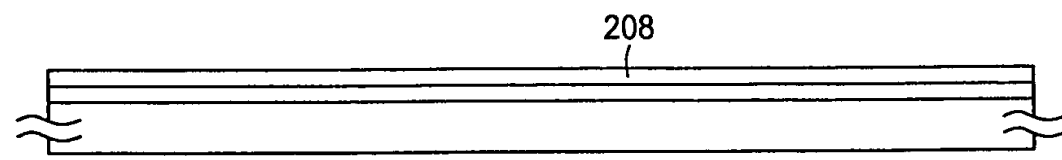


FIG. 2D

FORMATION OF WET OXIDE FILM
CONTAINING FLUORITE

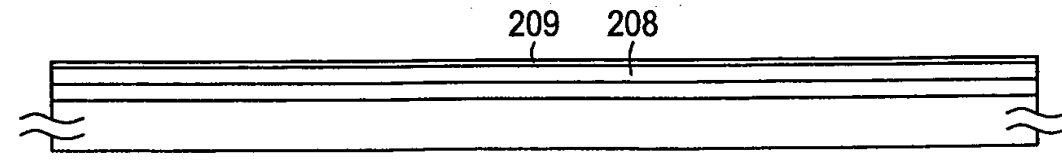
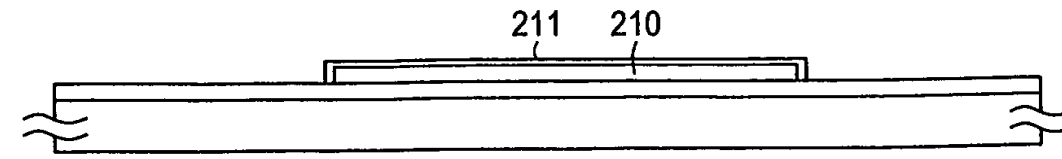


FIG. 2E



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FIG. 3A

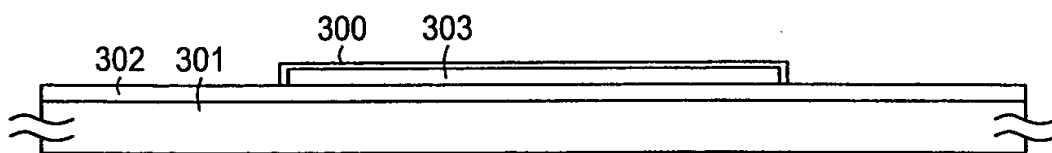


FIG. 3B

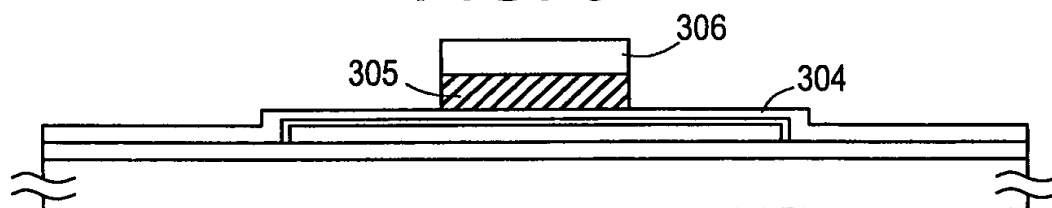


FIG. 3C

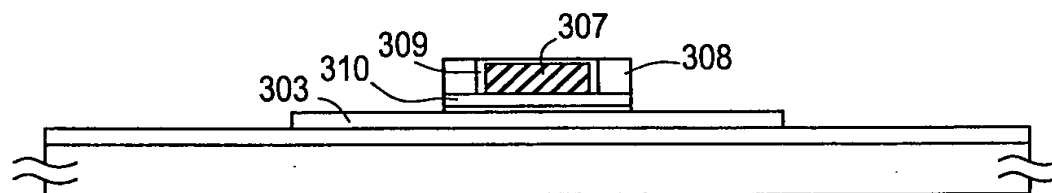


FIG. 3D

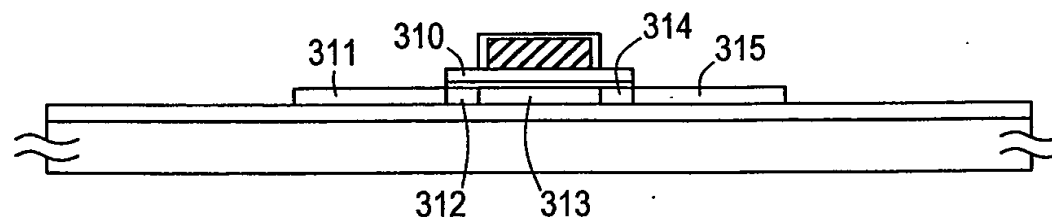


FIG. 3E

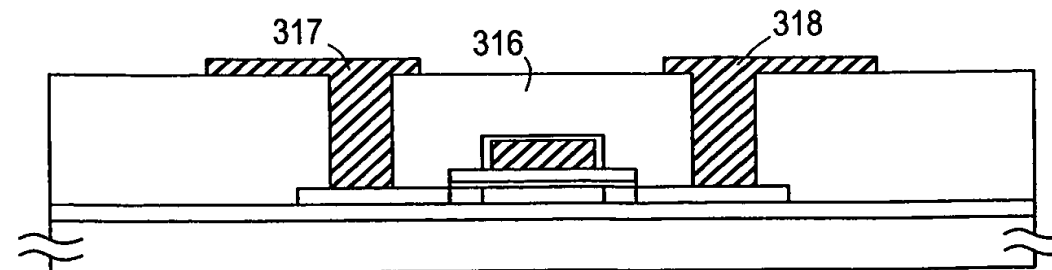


FIG. 4A

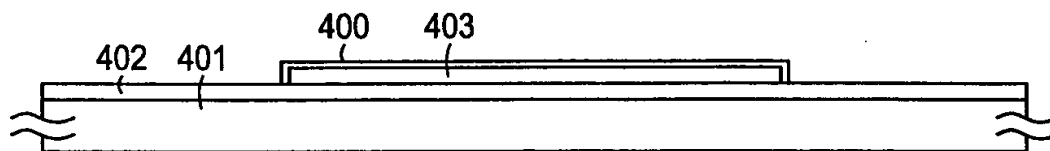


FIG. 4B

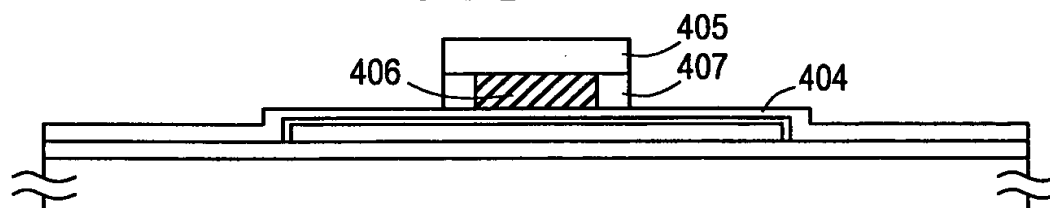


FIG. 4C

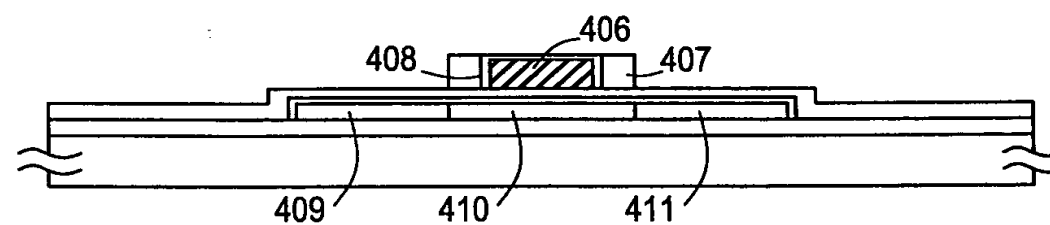


FIG. 4D

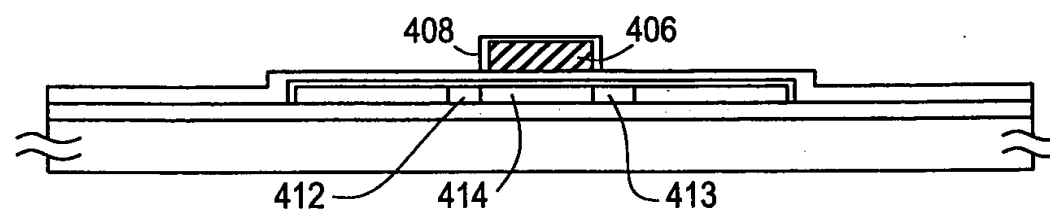


FIG. 4E

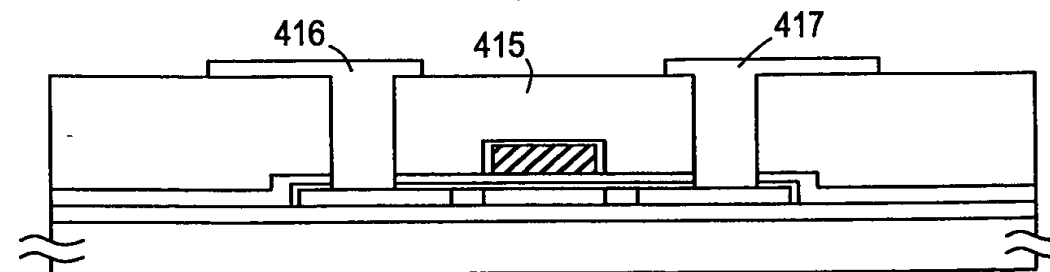


FIG. 5A

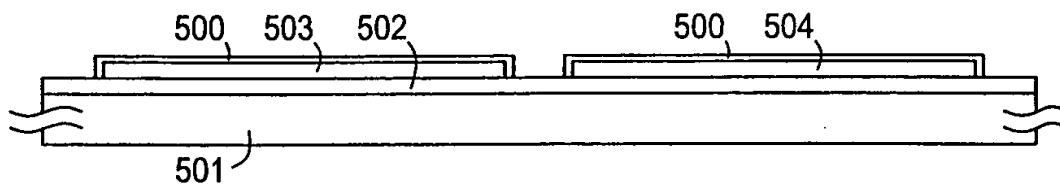


FIG. 5B

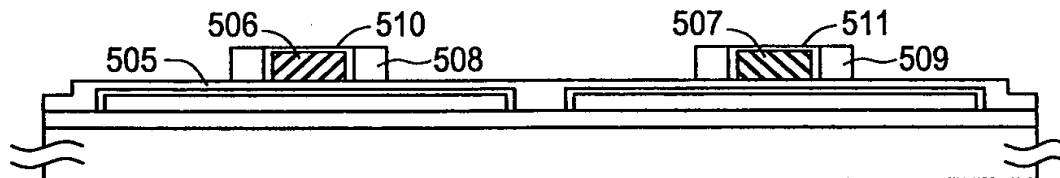


FIG. 5C

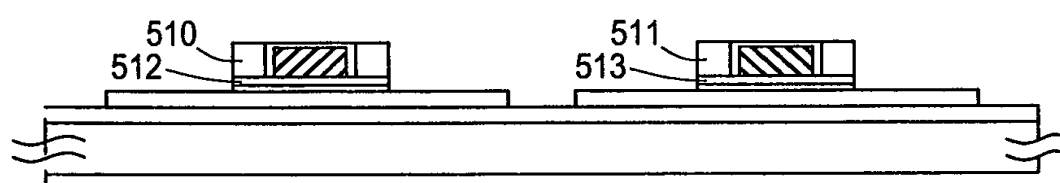


FIG. 5D

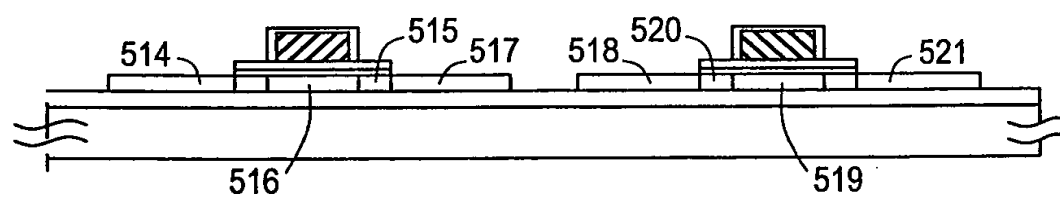


FIG. 5E

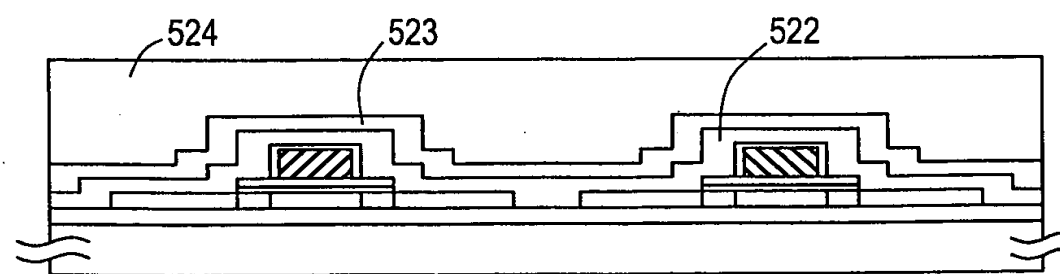


FIG. 5F

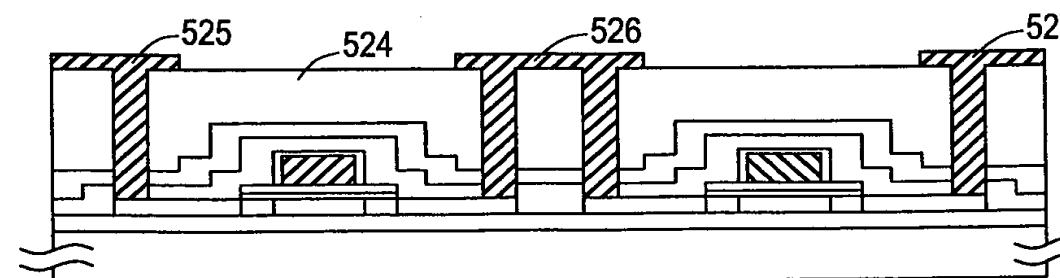


FIG. 6A

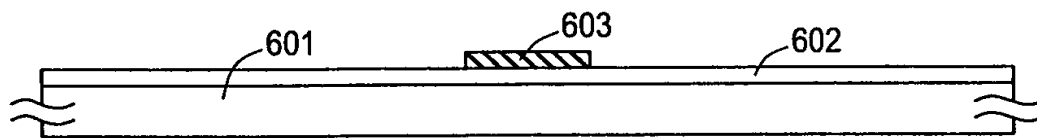


FIG. 6B

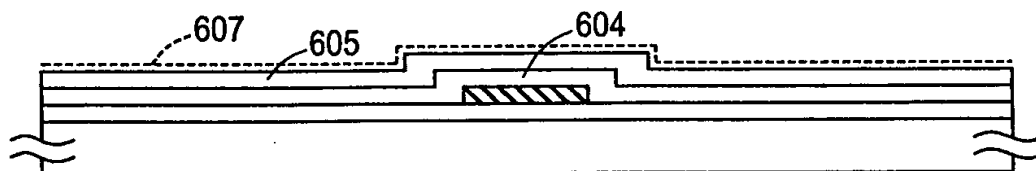


FIG. 6C

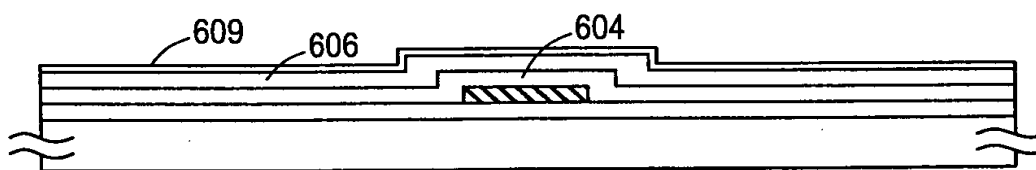


FIG. 6D

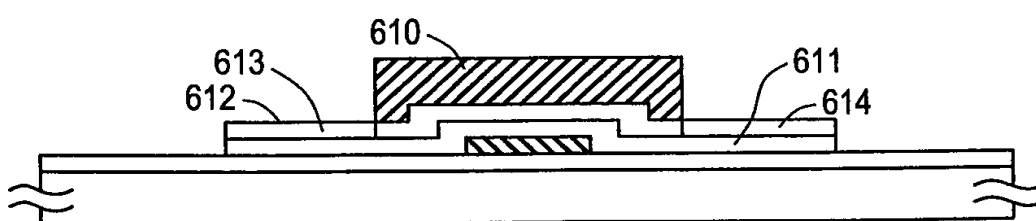


FIG. 6E

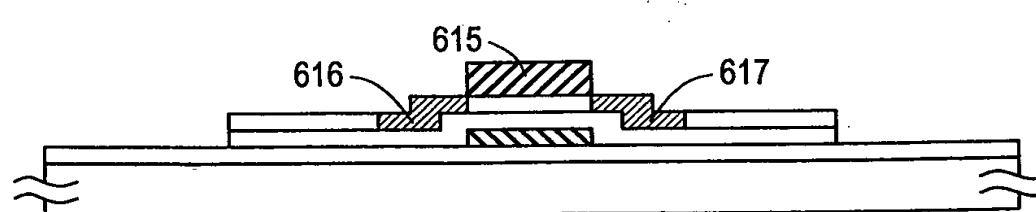


FIG. 6F

